

METHOD FOR MEASURING THE DEPTH OF A TRENCH IN THE SURFACE OF SEMICONDUCTOR WAFER

Abstract

A method for measuring the depth of a trench in a semiconductor wafer uses an optical apparatus to illuminate the wafer in the region of a trench and collects information in the interference of light reflected from the bottom of the trench and the nearby surface of the wafer. The trench width is small enough that the light reflected from the top and bottom of the trench is coherent.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)